

**ABSTRACT**

A pn-junction compound semiconductor light-emitting device is provided, which comprises a stacked structure including a light-emitting layer composed of an n-type or a p-type aluminum gallium indium phosphide and a light-permeable substrate for supporting the stacked structure, and the stacked structure and the light-permeable substrate being joined together, wherein the stacked structure includes an n-type or a p-type conductor layer, the conductor layer and the substrate are joined together, and the conductor layer is composed of a Group III-V compound semiconductor containing boron.